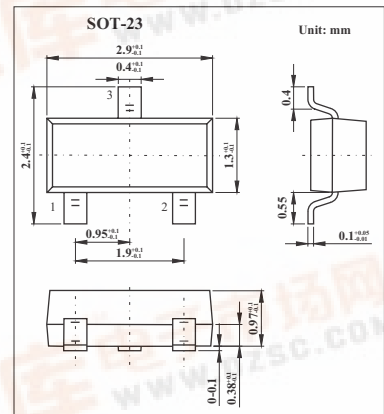


SMD Type Diodes

Silicon Schottky Barrier Diode
HRW0503A

Features

- Low forward voltage drop and suitable for high efficiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	VRRM	30	V
Average rectified current	Io	500	mA
Non-repetitive peak forward surge current	IFSM (Not e 1)	5	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to + 125	°C

Note

1. 50Hz sine wave 1 pulse

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 500 mA			0.55	V
Reverse current	IR	VR = 30 V			50	μ A
Capacitance	C	VR = 0 V, f = 1MHz		65		pF

Marking

Marking	S6
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